

Description

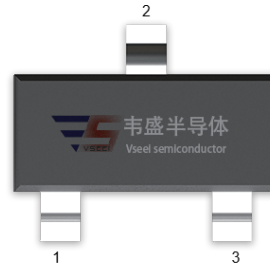
The VSM4003 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a Battery protection or in other switching application.

General Features

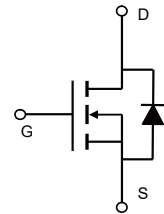
- $V_{DS} = 40V, I_D = 3A$
 $R_{DS(ON)} = 33m\Omega @ V_{GS}=10V(Typ)$
 $R_{DS(ON)} = 52m\Omega @ V_{GS}=4.5V(Typ)$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- DC/DC converter



SOT-23



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM4003	VSM4003-S2	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3	A
Drain Current-Pulsed (Note 1)	I_{DM}	10	A
Single pulse avalanche energy (Note 5)	E_{AS}	15	mJ
Maximum Power Dissipation	P_D	0.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	179	$^{\circ}C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	33	40	mΩ
		V _{GS} =4.5V, I _D =1A	-	52	68	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A	-	6	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	265	-	PF
Output Capacitance	C _{oss}		-	35	-	PF
Reverse Transfer Capacitance	C _{rss}		-	32	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, I _D =3A V _{GS} =10V, R _{GEN} =1Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	12	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =3A, V _{GS} =10V	-	10.2	-	nC
Gate-Source Charge	Q _{gs}		-	1.7	-	nC
Gate-Drain Charge	Q _{gd}		-	2.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25Ω

Typical Electrical and Thermal Characteristics

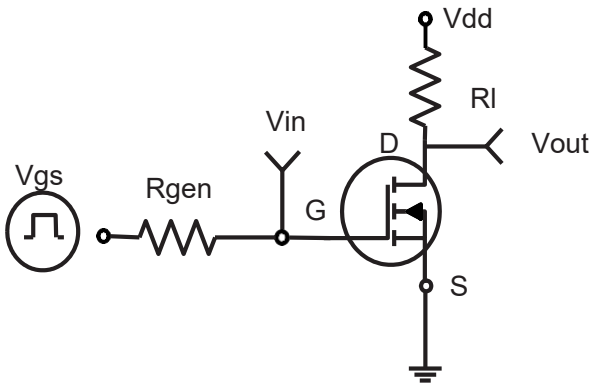


Figure 1: Switching Test Circuit

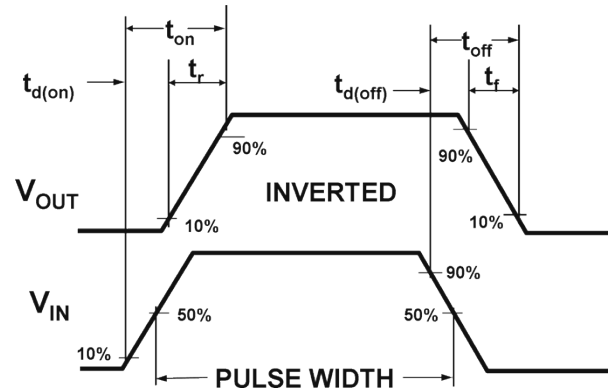


Figure 2: Switching Waveforms

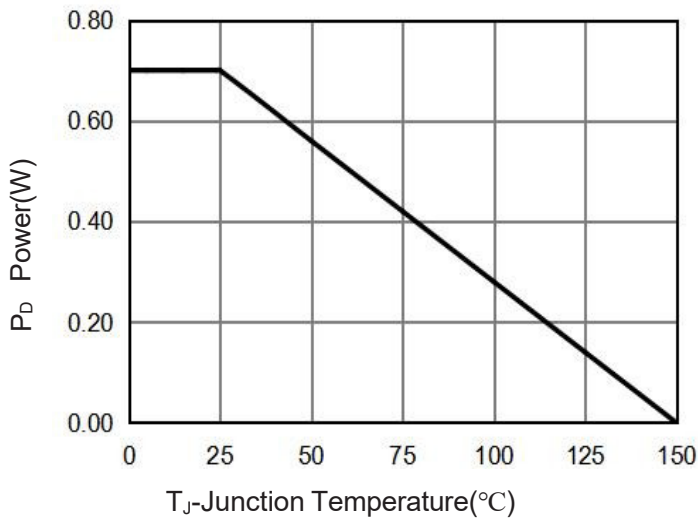


Figure 3 Power Dissipation

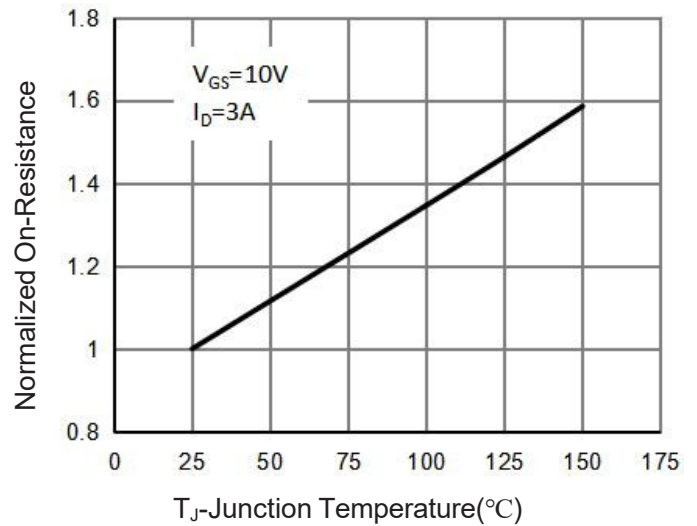


Figure 4 Drain-Source On-Resistance

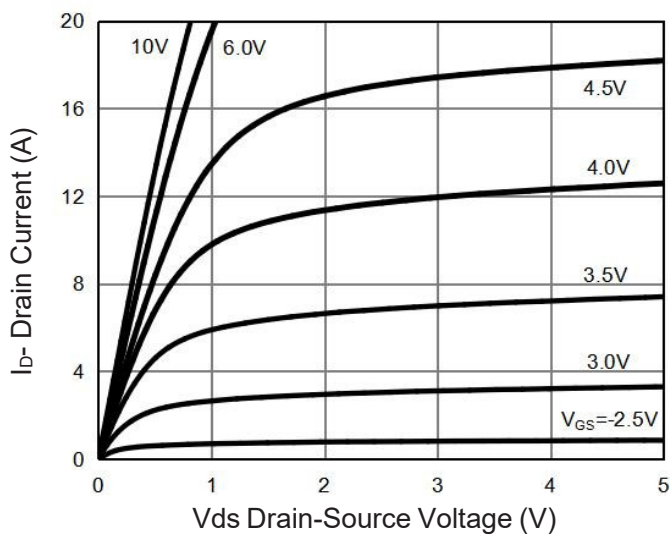


Figure 5 Output Characteristics

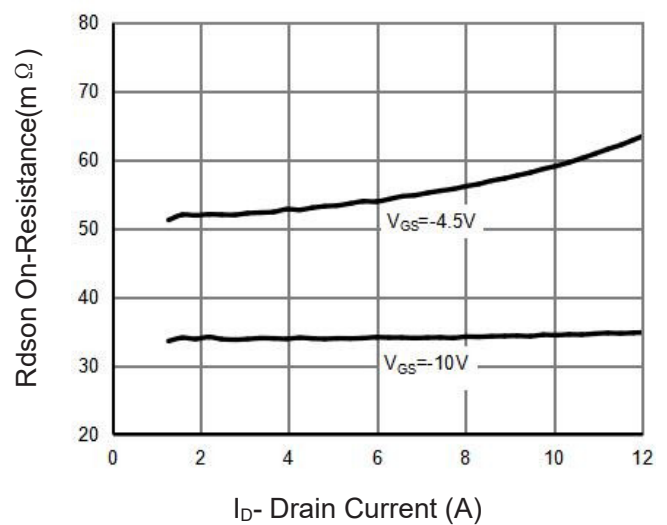
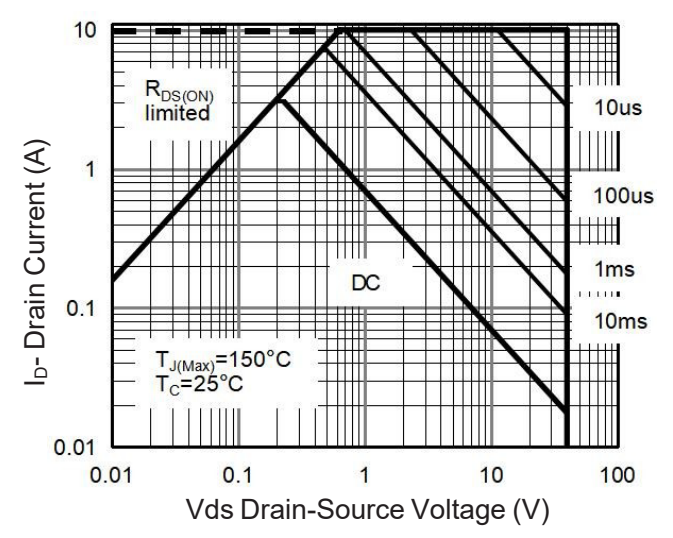
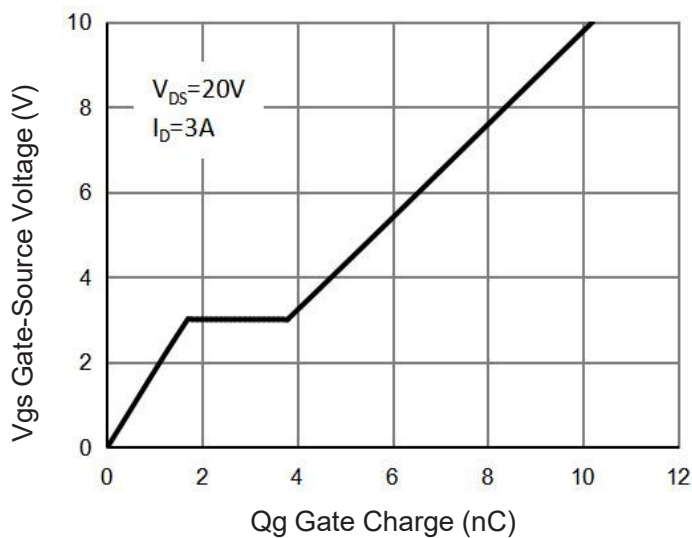
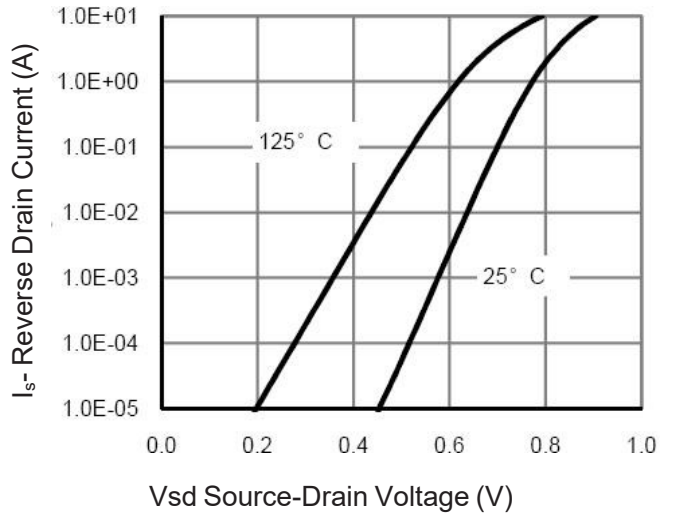
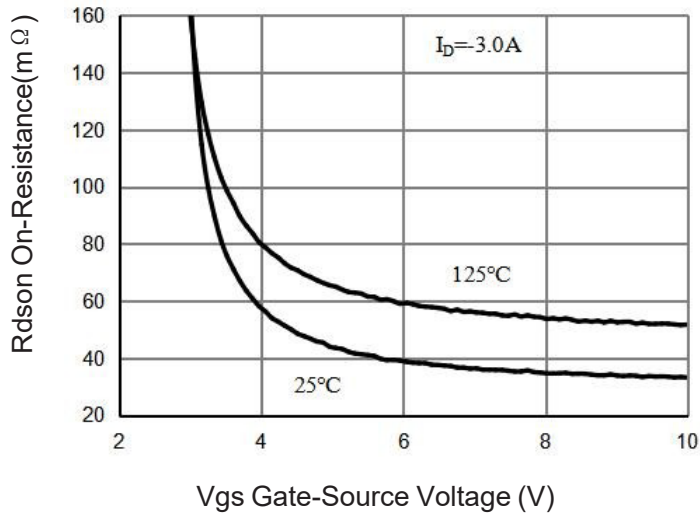
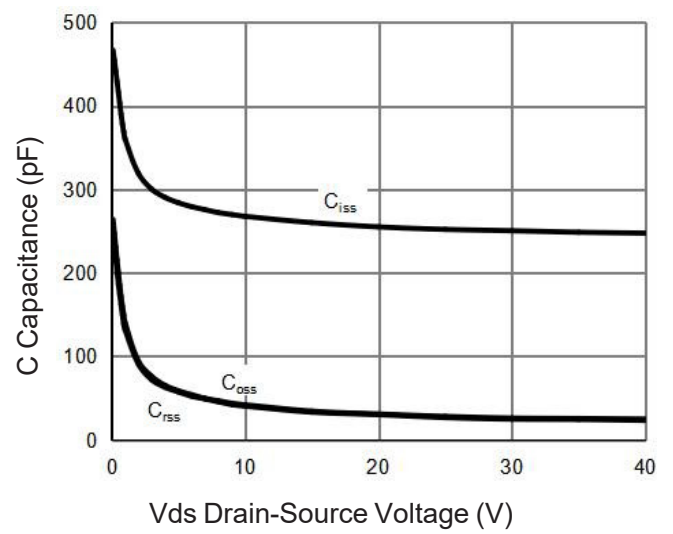
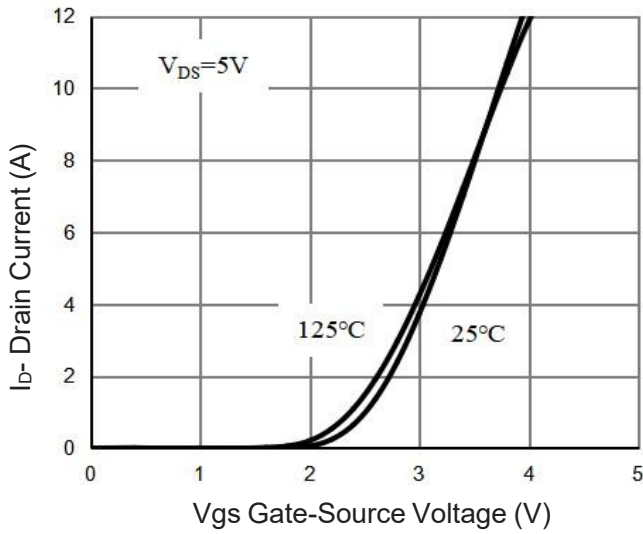


Figure 6 Drain-Source On-Resistance



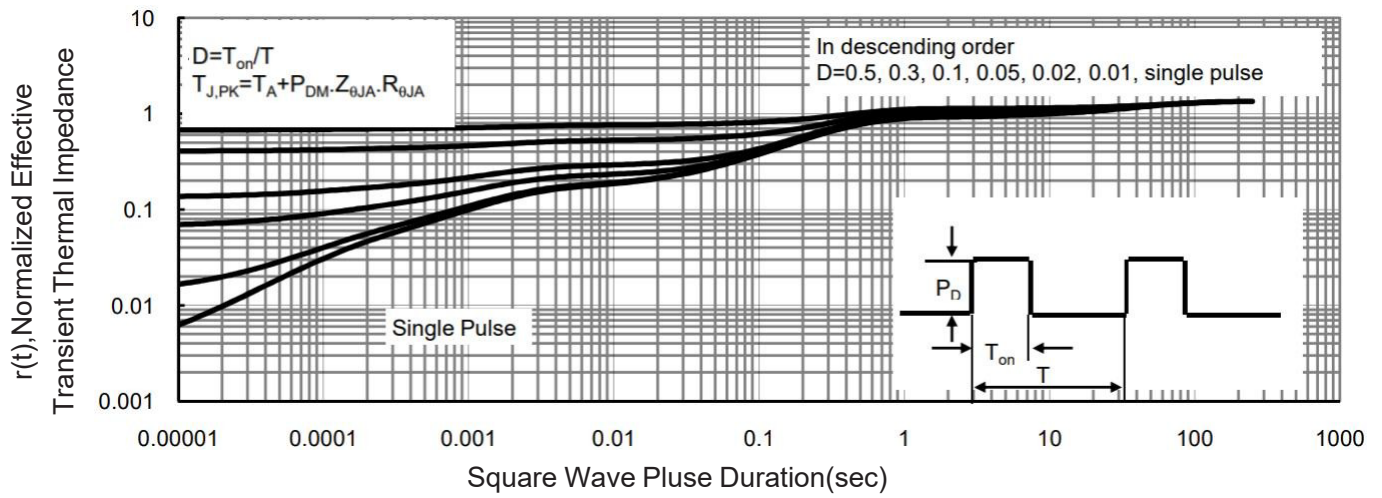


Figure 13 Normalized Maximum Transient Thermal Impedance